

Form PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Document Number (Optional)

NUS-03-001

Application Number

10/802,563

Applicant

Hong Yun Yu et al.

Filing Date

03/17/04

Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SK	62251685	1/1/01	Gardner et al.	438	287	6/4/98
SK	6383879	5/7/02	Kizilyalli et al.	438	303	5/17/00
SK	6511911	1/28/03	Besser et al.	438	656	4/3/01
SK	6617624	9/9/03	Powell	257	288	3/15/01
SK	6043157	3/28/00	Gardner et al.	438	692	12/18/97
SK	5960270	9/28/99	Misra et al.	438	197	8/11/97
SK	6083836	7/4/00	Rodder	438	690	12/18/98
SK	6576967	6/10/03	Schaeffer, III et al.	257	411	9/18/00
SK	6479362	11/12/02	Cunningham	438	369	2/14/01
SK	6208004	3/27/01	Cunningham	257	413	8/19/98
SK	6051487	4/18/00	Gardner et al.	438	585	12/18/97

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SK	-	Heuss et al., Abstract C7.6 "Thermal Stability of Hafnium and Hafnium Nitride (HfN _x) Gate Electrodes on Silicon Dioxide," pp. 67, 76-77, Materials Res. Soc. Proc., April 2000.
SK	-	"Physical and Electrical Properties of Metal Gate Electrodes on HfO ₂ Gate Dielectrics," by J.K. Schaeffer et al., Journal of Vacuum Science and Tech., Vol. 21(1), Jan/Feb. 2003, pp. 11-17.

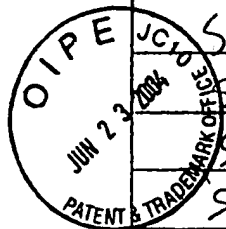
EXAMINER

LJW

DATE CONSIDERED

11/09/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.



(Use several sheets if necessary)

Application Number

10/802,563

Hong Yu Yu et al.

03717/04

Group Art Unit

[illegible][illegible]

SK	-	"Thermal Stability of PVD TiN Gate and Its Impacts Characteristics of CMOS Transistors," by M. Wang et al.
SK		6th Int'l Symp. on Plasma Process Induced Damage, Mar. 2001, Monterey, CA, USA, pp. 36-39.
SK	-	"Metal Gates for Advanced Sub-80-nm SOI CMOS Technol by B. Cheng et al., 2001 IEEE Int'l SOI Conf. 10/01, pp. 91-92

DATE CONSIDERED



11/09/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Doctor Number (Optional)

NUS-03-001

Application Number

10/802,563

Applicant:

Hong Yu Yu et al.

Filing Date

03/17/04

Group Art Unit

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Sr	-	"Properties and Microelectronic Applications of Thin Films of Refractory Metal Nitrides", by M. Wittmar, Jnl. of Vacuum Science Tech. A, Vol. 3, pp. 1797-1803.
Sr	-	"Int'l Tech. Roadmap for Semiconductor", Semiconductor Industry Association, San Jose, CA (ITRS-2003).

EXAMINER



DATE CONSIDERED

u/09/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant

(Use several sheets if necessary)

NUS-03-001

10/802,563

Hang Yu Yu et al.

03/17/04

Group Art Unit

[illegible][illegible]

SK	-	US Patent App. Pub. US 2003/0197230 A1 to Mocuta et al., Pub. Date 10/23/03, Filed 04/19/02, US Class 257/407.
SK	-	US Patent App. Pub. US 2002/0037615 A1 to Matsuo, Pub. Date 03/28/02, Filed 09/25/01, US Class 438/241.



DERED
11/09/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.